matched dual n-channel JFETs *designed for . . .*

■ VHF/UHF Amplifiers

Performance Curves NZF
See Section 4

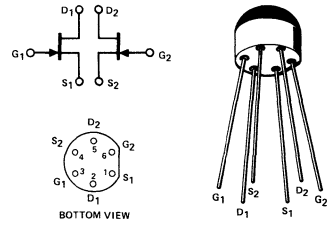
BENEFITS

- High Gain
  g_{fs} = 4500 μmho Minimum
- Dual Version of E300 with Matched Gate-to-Source Voltage

ABSOLUTE MAXIMUM RATINGS (25°C)

Gate-To-Gate Voltage . . . . . ±50 V
Gate-Drain or Gate-Source Voltage . . . . . -25 V
Gate Current . . . . . 50 mA
Total Package Dissipation
(25°C Free-Air Temperature) . . . . . 350 mW
Power Derating (to +125°C) . . . . . 3.5 mW/°C
Storage Temperature Range . . . . . -55 to +125°C
Operating Temperature Range . . . . . -55 to +125°C
Lead Temperature
(1/16" from case for 10 seconds) . . . . . 300°C

Si-200
See Section 5



ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

		Characteristic		E420 Min	E420 Typ	E420 Max	E421 Min	E421 Typ	E421 Max	Unit	Test Conditions	
1	STATIC	I_{GSS}	Gate Reverse Current (Note 1)			-500			-500	pA	V_{DS} = 0, V_{GS} = -15 V	
2	STATIC	$V_{GS(off)}$	Gate-Source Cutoff Voltage	-1		-6	-1		-6	V	V_{DS} = 10 V, I_D = 1 nA	
3	STATIC	BV_{GSS}	Gate-Source Breakdown Voltage	-25			-25			V	V_{DS} = 0, I_G = -1 μA	
4	STATIC	I_{DSS}	Saturation Drain Current (Note 2)	6		30	6		30	mA	V_{DS} = 10 V, V_{GS} = 0	
5	STATIC	I_G	Gate Current (Note 1)			-500			-500	pA	V_{DG} = 10 V, I_D = 5 mA	
6	DYNAMIC	g_{fs}	Common-Source Forward Transconductance	4,500		9,000	4,500		9,000	μmho	V_{DG} = 10 V, I_D = 5 mA	f = 1 kHz
7	DYNAMIC	g_{os}	Common-Source Output Conductance			200			200	μmho	V_{DG} = 10 V, I_D = 5 mA	f = 1 kHz
8	DYNAMIC	C_{iss}	Common-Source Input Capacitance		3.5			3.5		pF	V_{DG} = 10 V, I_D = 5 mA	f = 1 MHz
9	DYNAMIC	C_{rss}	Common-Source Reverse Transfer Capacitance		0.8			0.8		pF	V_{DG} = 10 V, I_D = 5 mA	f = 1 MHz
10	MAT	$\lvert V_{GS1}-V_{GS2}\rvert$	Differential Gate-Source Voltage			10			20	mV	V_{DG} = 10 V, I_D = 5 mA	

NZF

NOTES:
1. Approximately doubles for every 10°C increase in T_A.
2. Pulse test duration = 300 μsec; duty cycle ≤ 3%.